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Data Sheet November 2013

## 8 A, 1200 V, Hyperfast Diode

The RHRP8120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

## **Ordering Information**

PART NUMBER	PACKAGE	BRAND	
RHRP8120	TO-220AC-2L	RHRP8120	

NOTE: When ordering, use the entire part number.

## Symbol



#### **Features**

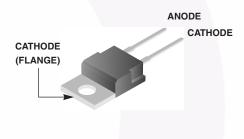
- Hyperfast Recovery t<sub>rr</sub> = 70 ns (@ I<sub>F</sub>= 8 A)
- Max Forward Voltage, V<sub>F</sub> = 3.2 V (@ T<sub>C</sub> = 25°C)
- 1200 V Reverse Voltage and High Reliability
- · Avalanche Energy Rated
- RoHS Compliant

## **Applications**

- · Switching Power Supplies
- Power Switching Circuits
- · General Purpose

## **Packaging**

**JEDEC TO-220AC** 



<b>Absolute Maximum Ratings</b> $T_C = 25^{\circ}C$ , Unless Otherwise Specified		
	RHRP8120	UNIT
Peak Repetitive Reverse Voltage	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking VoltageV <sub>R</sub>	1200	V
Average Rectified Forward Current $I_{F(AV)}$ ( $T_C = 140^{\circ}C$ )	8	Α
Repetitive Peak Surge Current	16	Α
Nonrepetitive Peak Surge Current	100	Α
Maximum Power Dissipation	75	W
Avalanche Energy (See Figures 10 and 11)	20	mJ
Operating and Storage Temperature	-65 to 175	°С

**Electrical Specifications** T<sub>C</sub> = 25°C, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
V <sub>F</sub>	I <sub>F</sub> = 8 A	-	-	3.2	V
	$I_F = 8 \text{ A}, T_C = 150^{\circ}\text{C}$	-	-	2.6	V
I <sub>R</sub>	V <sub>R</sub> = 1200 V	-	-	100	μΑ
	$V_R = 1200 \text{ V}, T_C = 150^{\circ}\text{C}$	-	-	500	μΑ
t <sub>rr</sub>	I <sub>F</sub> = 1 A, dI <sub>F</sub> /dt = 200 A/μs	-	-	55	ns
	$I_F = 8 \text{ A}, dI_F/dt = 200 \text{ A}/\mu\text{s}$	-	-	70	ns
t <sub>a</sub>	I <sub>F</sub> = 8 A, dI <sub>F</sub> /dt = 200 A/μs	-	30	-	ns
t <sub>b</sub>	I <sub>F</sub> = 8 A, dI <sub>F</sub> /dt = 200 A/μs	-	20	-	ns
Q <sub>rr</sub>	$I_F = 8 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	165	-	nC
СЈ	V <sub>R</sub> = 10 V, I <sub>F</sub> = 0 A	-	25	-	pF
$R_{ heta JC}$		-	-	2	°C/W

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300  $\mu$ s, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

 $T_{rr}$  = Reverse recovery time (See Figure 9), summation of  $t_a$  +  $t_b$ .

 $t_a$  = Time to reach peak reverse current (See Figure 9).

 $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

Q<sub>rr</sub> = Reverse Recovery Charge.

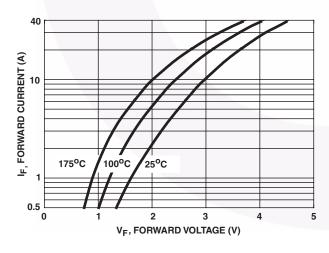
C<sub>J</sub> = Junction Capacitance.

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = Pulse Width.

D = Duty Cycle.

## Typical Performance Curves





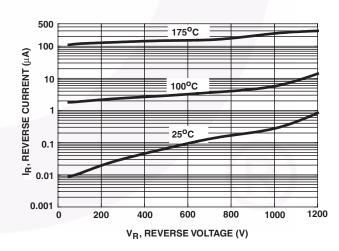


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

## Typical Performance Curves (Continued)

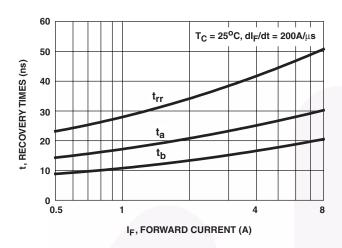


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

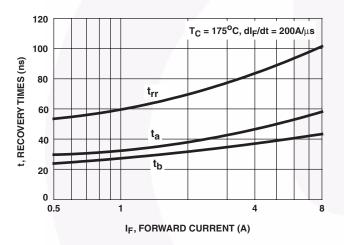


FIGURE 5. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

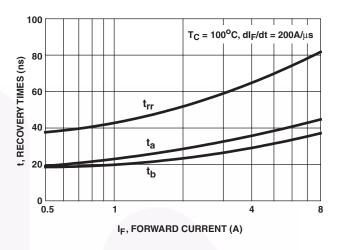


FIGURE 4. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

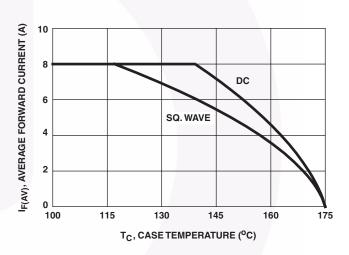


FIGURE 6. CURRENT DERATING CURVE

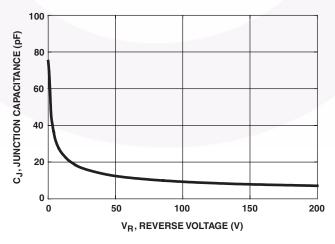


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

#### Test Circuits and Waveforms

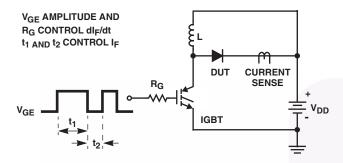


FIGURE 8. t<sub>rr</sub> TEST CIRCUIT

 $I_{MAX} = 1A$  L = 40mH  $R < 0.1\Omega$   $E_{AVL} = 1/2Li^2 \left[ V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]$   $Q_1 = IGBT \left( BV_{CES} > DUT V_{R(AVL)} \right)$  L R CURRENT + O  $SENSE V_{DD}$   $V_{DD}$   $O_1$   $O_1$   $O_2$   $O_3$   $O_4$   $O_5$   $O_6$   $O_7$   $O_8$   $O_8$   $O_8$   $O_9$   $O_9$ 

FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

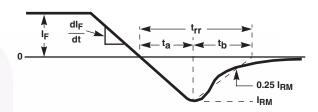


FIGURE 9. t<sub>rr</sub> WAVEFORMS AND DEFINITIONS

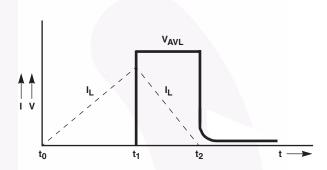
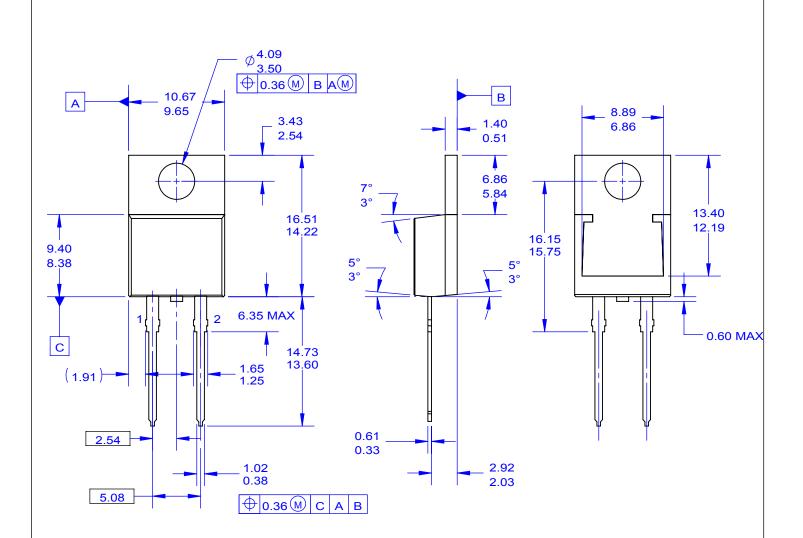
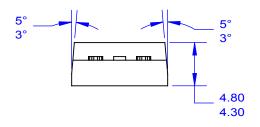


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS







#### **NOTES**:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
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